Kuan Y Cheong

List of Publications by Citations

207 papers	3,620 citations	27 h-index	50 g-index
230 ext. papers	4,189 ext. citations	3 avg, IF	5.79 L-index

#	Paper	IF	Citations
207	Die Attach Materials for High Temperature Applications: A Review. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2011**, 1, 457-478	1.7	254
206	A Review on Die Attach Materials for SiC-Based High-Temperature Power Devices. *Metallurgical and Materials Transactions B: Process Metallurgy and Materials Processing Science*, **2010**, 41, 824-832	2.5	207
205	Mechanisms responsible for improvement of 4H□SiC/SiO2 interface properties by nitridation. *Applied Physics Letters*, **2003**, 82, 568-570	3.4	170
204	Electrical and optical studies of ZnO:Ga thin films fabricated via the sol□gel technique. *Thin Solid Films*, **2002**, 410, 142-146	2.2	158
203	Advances of Ag, Cu, and Ag□Cu alloy nanoparticles synthesized via chemical reduction route. *Journal of Nanoparticle Research*, **2013**, 15, 1	2.3	115
202	Current conduction mechanisms in atomic-layer-deposited HfO2/nitrided SiO2 stacked gate on 4H silicon carbide. *Journal of Applied Physics*, **2008**, 103, 084113	2.5	110
201	Advances of SiC-based MOS capacitor hydrogen sensors for harsh environment applications. *Sensors and Actuators B: Chemical*, **2010**, 151, 39-55	8.5	80
200	Effects of drying temperature and ethanol concentration on bipolar switching characteristics of natural Aloe vera-based memory devices. *Physical Chemistry Chemical Physics*, **2015**, 17, 26833-53	3.6	78
199	Electrical and physical characterization of gate oxides on 4H-SiC grown in diluted N2O. *Journal of Applied Physics*, **2003**, 93, 5682-5686	2.5	69
198	A review on the synthesis of SiC from plant-based biomasses. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2011**, 176, 951-964	3.1	65
197	Effects of Postdeposition Annealing in Argon Ambient on Metallorganic Decomposed CeO[sub 2] Gate Spin Coated on Silicon. *Journal of the Electrochemical Society*, **2010**, 157, H6	3.9	52
196	Wettability and strength of In□Bi□Sn lead-free solder alloy on copper substrate. *Journal of Alloys and Compounds*, **2010**, 507, 290-296	5.7	50
195	Elaboration and characterization of sol□gel derived ZrO2 thin films treated with hot water. *Applied Surface Science*, **2012**, 258, 5250-5258	6.7	47
194	Chemical reduction methods for synthesizing Ag and Al nanoparticles and their respective nanoalloys. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2011**, 176, 187-203	3.1	47
193	Review on oxides of antimony nanoparticles: synthesis, properties, and applications. *Journal of Materials Science*, **2010**, 45, 5993-6008	4.3	43
192	Polymorphisms in lymphotoxin alpha and CD14 genes influence TNFalpha production induced by Gram-positive and Gram-negative bacteria. *Genes and Immunity*, **2003**, 4, 283-8	4.4	42
191	Sm2O3 gate dielectric on Si substrate. *Materials Science in Semiconductor Processing*, **2010**, 13, 303-314	4.3	41

190	ZrO2 thin films on Si substrate. *Journal of Materials Science: Materials in Electronics*, **2010**, 21, 980-993	2.1	39
189	Effects of post-deposition annealing ambient on Y2O3 gate deposited on silicon by RF magnetron sputtering. *Journal of Alloys and Compounds*, **2012**, 529, 73-83	5.7	35
188	Synthesis of Zn(II) 5,10,15,20-tetrakis(4?-isopropylphenyl) porphyrin and its use as a thin film sensor. *Applied Physics A: Materials Science and Processing*, **2010**, 98, 103-109	2.6	35
187	Localization of central MHC genes influencing type I diabetes. *Human Immunology*, **2001**, 62, 1363-70	2.3	35
186	Thermal oxidation and nitridation of sputtered Zr thin film on Si via N2O gas. *Journal of Alloys and Compounds*, **2011**, 509, 8728-8737	5.7	33
185	Comparison of metal-organic decomposed (MOD) cerium oxide (CeO2) gate deposited on GaN and SiC substrates. *Journal of Crystal Growth*, **2011**, 326, 2-8	1.6	33
184	Analysis of current conduction mechanisms in atomic-layer-deposited Al2O3 gate on 4H silicon carbide. *Applied Physics Letters*, **2007**, 90, 162113	3.4	33
183	Electronic Properties of Atomic-Layer-Deposited Al[sub 2]O[sub 3]/Thermal-Nitrided SiO[sub 2] Stacking Dielectric on 4H SiC. *Electrochemical and Solid-State Letters*, **2007**, 10, H69		32
182	Improved Electronic Performance of $hbox{HfO}_{2}/ hbox{SiO}_{2}$ Stacking Gate Dielectric on 4H SiC. *IEEE Transactions on Electron Devices*, **2007**, 54, 3409-3413	2.9	28
181	Effects of thermal nitrided gate-oxide thickness on 4H silicon-carbide-based metal-oxide-semiconductor characteristics. *Applied Physics Letters*, **2007**, 90, 012120	3.4	28
180	Embedded Nanoparticles in Schottky and Ohmic Contacts: A Review. *Critical Reviews in Solid State and Materials Sciences*, **2015**, 40, 197-222	10.1	27
179	Microstructural and optical properties of ZrON/Si thin films. *Materials Letters*, **2013**, 105, 72-75	3.3	27
178	Effect of Postdeposition Annealing in Oxygen Ambient on Gallium-Nitride-Based MOS Capacitors With Cerium Oxide Gate. *IEEE Transactions on Electron Devices*, **2011**, 58, 122-131	2.9	27
177	Ultrathin Wafer Pre-Assembly and Assembly Process Technologies: A Review. *Critical Reviews in Solid State and Materials Sciences*, **2015**, 40, 251-290	10.1	25
176	Oxygen vacancy formation and annihilation in lanthanum cerium oxide as a metal reactive oxide on 4H-silicon carbide. *Physical Chemistry Chemical Physics*, **2014**, 16, 7015-22	3.6	25
175	Recent development of gallium oxide thin film on GaN. *Materials Science in Semiconductor Processing*, **2013**, 16, 1217-1231	4.3	25
174	Oxidation of sputtered Zr thin film on Si substrate. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 143-150	2.1	25
173	Electrical Properties of Pulsed Laser Deposited Y[sub 2]O[sub 3] Gate Oxide on 4H□SiC. *Electrochemical and Solid-State Letters*, **2010**, 13, H396		25

172	Deposition and post-deposition annealing of thin Y2O3 film on n-type Si in argon ambient. *Materials Chemistry and Physics*, **2011**, 130, 1007-1015	4.4	24
171	Investigation of forming-gas annealed CeO2 thin film on GaN. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 583-591	2.1	24
170	Metal-oxide-semiconductor characteristics of thermally grown nitrided SiO2 thin film on 4H-SiC in various N2O ambient. *Thin Solid Films*, **2010**, 518, 3255-3259	2.2	24
169	Thermal characteristic of sintered Ag-Cu nanopaste for high-temperature die-attach application. *International Journal of Thermal Sciences*, **2015**, 87, 169-177	4.1	23
168	Aloe vera gel as natural organic dielectric in electronic application. *Journal of Materials Science: Materials in Electronics*, **2013**, 24, 2646-2652	2.1	23
167	Physical and electrical characteristics of metal-organic decomposed CeO2 gate spin-coated on 4H-SiC. *Applied Physics A: Materials Science and Processing*, **2011**, 103, 1067-1075	2.6	23
166	Mechanical properties of sintered Ag-Cu die-attach nanopaste for application on SiC device. *Materials & Design*, **2014**, 64, 166-176		22
165	Effects of post-deposition annealing ambient on chemical, structural, and electrical properties of RF magnetron sputtered Y2O3 gate on gallium nitride. *Journal of Alloys and Compounds*, **2013**, 575, 382-392	5.7	22
164	Formation of Zr-oxynitride thin films on 4H-SiC substrate. *Thin Solid Films*, **2012**, 520, 6822-6829	2.2	22
163	Effects of post-oxidation annealing temperature on ZrO2 thin film deposited on 4H-SiC substrate. *Materials Science in Semiconductor Processing*, **2011**, 14, 13-17	4.3	22
162	Electrical Characteristics of Oxidized-Nitrided Zr Thin Film on Si. *Journal of the Electrochemical Society*, **2011**, 158, H1270	3.9	21
161	Effects of N2O Postdeposition Annealing on Metal-Organic Decomposed CeO2 Gate Oxide Spin-Coated on GaN Substrate. *Journal of the Electrochemical Society*, **2011**, 158, H423	3.9	21
160	Sintering of Silver-Aluminum Nanopaste With Varying Aluminum Weight Percent for Use as a High-Temperature Die-Attach Material. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2012**, 2, 1940-1948	1.7	21
159	Influence of post-deposition annealing in oxygen ambient on metal-organic decomposed CeO2 film spin coated on 4H-SiC. *Journal of Materials Science: Materials in Electronics*, **2012**, 23, 257-266	2.1	20
158	Physical characterization of post-deposition annealed metal-organic decomposed cerium oxide film spin-coated on 4H-silicon carbide. *Journal of Alloys and Compounds*, **2010**, 497, 195-200	5.7	20
157	Effects of post-deposition annealing temperature and time on physical properties of metal-organic decomposed lanthanum cerium oxide thin film. *Thin Solid Films*, **2011**, 519, 5139-5145	2.2	20
156	Analysis of charge conduction mechanisms in nitrided SiO2 Film on 4H SiC. *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2008**, 372, 529-532	2.3	20
155	Characterization Methods for Ultrathin Wafer and Die Quality: A Review. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2014**, 4, 2042-2057	1.7	19

154	MOS Characteristics of Metallorganic-Decomposed CeO[sub 2] Spin-Coated on GaN. *Electrochemical and Solid-State Letters*, **2010**, 13, H116		19
153	Effects of Post-Deposition Annealing on CeO2 Gate Prepared by Metal-Organic Decomposition (MOD) Method on 4H-SiC. *Materials Science Forum*, **2010**, 645-648, 837-840	0.4	19
152	Investigation of sol□gel derived HfO2 on 4H-SiC. *Applied Surface Science*, **2008**, 254, 1981-1985	6.7	19
151	Channel-carrier mobility parameters for 4H SiC MOSFETs. *Microelectronics Reliability*, **2003**, 43, 405-411	1.2	19
150	Physical and Electrical Characteristics of Silver-Copper Nanopaste as Alternative Die-Attach. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2014**, 4, 8-15	1.7	18
149	Physical and dispersive optical characteristics of ZrON/Si thin-film system. *Applied Physics A: Materials Science and Processing*, **2014**, 115, 1069-1072	2.6	18
148	Study on Gallium Nitride-Based Metal□Oxide□Semiconductor Capacitors With RF Magnetron Sputtered $hbox{Y}_{2}hbox{O}_{3}$ Gate. *IEEE Transactions on Electron Devices*, **2012**, 59, 3009-3016	2.9	18
147	Metal-oxide-semiconductor characteristics of lanthanum cerium oxide film on Si. *Applied Physics A: Materials Science and Processing*, **2012**, 107, 459-467	2.6	18
146	Structural and Chemical Studies of Metal□Organic Decomposed LaxCeyOz Thin Film as a Catalytic Oxide on 4H-SiC as a Function of Postdeposition Annealing Time. *Journal of Physical Chemistry C*, **2013**, 117, 14014-14024	3.8	18
145	Band alignment and enhanced breakdown field of simultaneously oxidized and nitrided Zr film on Si. *Nanoscale Research Letters*, **2011**, 6, 489	5	18
144	Metal-Oxide-Semiconductor Characteristics of Zr-Oxynitride Thin Film on 4H-SiC Substrate. *Journal of the Electrochemical Society*, **2012**, 159, H293-H299	3.9	18
143	MOS capacitor on 4H-SiC as a nonvolatile memory element. *IEEE Electron Device Letters*, **2002**, 23, 404-406	4.4	18
142	Effects of annealing time on the electrical properties of the Y2O3 gate on silicon. *Journal of Experimental Nanoscience*, **2015**, 10, 19-28	1.9	17
141	Growth of SiC nanowires and nanocones using mixture of oil palm fibres and rice husk ash. *Journal of Materials Science*, **2012**, 47, 5477-5487	4.3	17
140	Gold nanoparticles deposited on linker-free silicon substrate and embedded in aluminum Schottky contact. *Journal of Colloid and Interface Science*, **2013**, 408, 220-8	9.3	16
139	Effects of post-deposition annealing temperature on metal-organic decomposed lanthanum cerium oxide film as metal reactive oxide layer on 4H-SiC. *Materials Chemistry and Physics*, **2013**, 140, 622-633	4.4	16
138	Study of molar ratio on the characteristics of metal□rganic decomposed LaxCe1□xOz film as a metal reactive oxide on Si substrate. *Journal of Alloys and Compounds*, **2013**, 581, 793-800	5.7	16
137	Surface passivation of gallium nitride by ultrathin RF-magnetron sputtered Al2O3 gate. *ACS Applied Materials & Interfaces*, **2013**, 5, 6860-3	9.5	16

136	Rapid formation of transparent CuAlO2 thin film by thermal annealing of Cu on Al2O3. *Solar Energy Materials and Solar Cells*, **2009**, 93, 1383-1387	6.4	16
135	Filamentary Conduction in Aloe Vera Film for Memory Application. *Procedia Engineering*, **2017**, 184, 655-662		15
134	Investigation of Aloe Vera as active layer for development of organic based memory devices. *Materials Technology*, **2015**, 30, A29-A35	2.1	15
133	Reliability of sintered Ag80Al20 die attach nanopaste for high temperature applications on SiC power devices. *Microelectronics Reliability*, **2013**, 53, 473-480	1.2	15
132	Effects of post-deposition annealing temperature and ambient on RF magnetron sputtered Sm2O3 gate on n-type silicon substrate. *Journal of Materials Science: Materials in Electronics*, **2011**, 22, 1816-1826	2.1	15
131	Ag/PEPC/NiPc/ZnO/Ag thin film capacitive and resistive humidity sensors. *Journal of Semiconductors*, **2010**, 31, 054002	2.3	15
130	Stimulation of silicon carbide nanotubes formation using different ratios of carbon nanotubes to silicon dioxide nanopowders. *Journal of Alloys and Compounds*, **2009**, 475, 565-568	5.7	15
129	Formation and characterization of SiOx nanowires and Si/SiOx core-shell nanowires via carbon-assisted growth. *Physica E: Low-Dimensional Systems and Nanostructures*, **2010**, 42, 1338-1342	3	15
128	Effects of rapid thermal annealing on nitrided gate oxide grown on 4H-SiC. *Microelectronic Engineering*, **2006**, 83, 65-71	2.5	15
127	Current conduction mechanisms in post-nitridation rapid-thermal-annealed gate oxides on 4H silicon carbide. *Applied Physics Letters*, **2005**, 87, 212102	3.4	15
126	Retardation mechanism of ultrathin Al2O3 interlayer on Y2O3 passivated gallium nitride surface. *ACS Applied Materials & Interfaces*, **2014**, 6, 7797-805	9.5	14
125	Effects of annealing temperature on ultra-low dielectric constant SiO2 thin films derived from sol–gel spin-on-coating. *Physica B: Condensed Matter*, **2008**, 403, 611-615	2.8	14
124	Investigation of ultralow leakage in MOS capacitors on 4H SiC. *IEEE Transactions on Electron Devices* , **2004**, 51, 1361-1365	2.9	14
123	Current conduction mechanisms of RF-Magnetron sputtered Y2O3 gate oxide on gallium nitride. *Current Applied Physics*, **2013**, 13, 1433-1439	2.6	13
122	N-Type Organic Field-Effect Transistor Based on Fullerene with Natural Aloe Vera/SiO2Nanoparticles as Gate Dielectric. *ECS Journal of Solid State Science and Technology*, **2013**, 2, P440-P444	2	13
121	Charge retention in metal–oxide–semiconductor capacitors on SiC used as nonvolatile-memory elements. *Applied Physics Letters*, **2002**, 80, 3421-3423	3.4	13
120	Effects of post-deposition annealing time in oxygen ambient on Y2O3 film deposited on silicon substrate. *Materials Research Innovations*, **2014**, 18, S6-495-S6-498	1.9	12
119	Controlled synthesis of Sb2O3 nanoparticles by chemical reducing method in ethylene glycol. *Journal of Nanoparticle Research*, **2011**, 13, 2807-2818	2.3	12

118	Effect of post-deposition annealing temperature on CeO2 thin film deposited on silicon substrate via RF magnetron sputtering technique. *Materials Science in Semiconductor Processing*, **2011**, 14, 101-107	4.3	12
117	Can MHC class II genes mediate resistance to type 1 diabetes?. *Immunology and Cell Biology*, **2001**, 79, 602-6	5	12
116	Au nanoparticles embedded at the interface of Al/4H-SiC Schottky contacts for current density enhancement. *Applied Physics A: Materials Science and Processing*, **2015**, 118, 315-325	2.6	11
115	Effects of post-deposition annealing ambient on band alignment of RF magnetron-sputtered Y2O3 film on gallium nitride. *Nanoscale Research Letters*, **2013**, 8, 53	5	11
114	Effect of Postoxidation Annealing on High Temperature Grown SiO[sub 2]/4H-SiC Interfaces. *Journal of the Electrochemical Society*, **2010**, 157, H196	3.9	11
113	Effects of Electrode Materials on Charge Conduction Mechanisms of Memory Device Based on Natural Aloe Vera. *MRS Advances*, **2016**, 1, 2513-2518	0.7	11
112	Review on resistive switching mechanisms of bio-organic thin film for non-volatile memory application. *Nanotechnology Reviews*, **2021**, 10, 680-709	6.3	11
111	Switching Dynamics and Conductance Quantization of $Aloe$ Polysaccharides-Based Device. *IEEE Transactions on Electron Devices*, **2019**, 66, 3110-3117	2.9	10
110	Physical and electrical attributes of sintered Ag80Al20 high temperature die attach material with different organic additives content. *Journal of Materials Science: Materials in Electronics*, **2013**, 24, 720-733	2.1	10
109	Growth Mechanism of Cubic-Silicon Carbide Nanowires. *Journal of Nanomaterials*, **2009**, 2009, 1-5	3.2	10
108	Characterization of anodic SiO2 films on P-type 4H-SiC. *Thin Solid Films*, **2009**, 517, 2808-2812	2.2	10
107	Investigation of electron-hole generation in MOS capacitors on 4H SiC. *IEEE Transactions on Electron Devices*, **2003**, 50, 1433-1439	2.9	10
106	Nonvolatile Memory Device Based on Bipolar and Unipolar Resistive Switching in Bio-Organic Aloe Polysaccharides Thin Film. *Advanced Materials Technologies*, **2018**, 3, 1800007	6.8	10
105	Characterization of ultrathin Al2O3 gate oxide deposited by RF-magnetron sputtering on gallium nitride epilayer on sapphire substrate. *Materials Chemistry and Physics*, **2014**, 148, 592-604	4.4	9
104	Thermal and photo reversible gel–sol transition of azobenzene based liquid crystalline organogel. *Journal of Photochemistry and Photobiology A: Chemistry*, **2014**, 278, 19-24	4.7	9
103	Fabrication of well-crystallized mesoporous ZrO2 thin films via Pluronic P123 templated sol–gel route. *Ceramics International*, **2013**, 39, S437-S440	5.1	9
102	Design of hierarchically meso–macroporous tetragonal ZrO2 thin films with tunable thickness by spin-coating via sol–gel template route. *Microporous and Mesoporous Materials*, **2013**, 167, 198-206	5.3	9
101	Effect of Sintering Temperature on Silver-Copper Nanopaste as High Temperature Die Attach Material. *Advanced Materials Research*, **2013**, 795, 47-50	0.5	9

100	Post deposition annealing effect on properties of Y2O3/Al2O3 stacking gate dielectric on 4H-SiC. *Materials Letters*, **2019**, 245, 174-177	3.3	8
99	Effects of rapid thermal annealing on structural, chemical, and electrical characteristics of atomic-layer deposited lanthanum doped zirconium dioxide thin film on 4H-SiC substrate. *Applied Surface Science*, **2016**, 365, 296-305	6.7	8
98	The effect of size and shape of gold nanoparticles on thin film properties. *Journal of Experimental Nanoscience*, **2014**, 9, 64-77	1.9	8
97	Growth of SiC nanowires using oil palm empty fruit bunch fibres infiltrated with tetraethyl orthosilicate. *Physica E: Low-Dimensional Systems and Nanostructures*, **2012**, 44, 2041-2049	3	8
96	Direct formation of gold nanoparticles on substrates using a novel ZnO sacrificial templated-growth hydrothermal approach and their properties in organic memory device. *Nanoscale Research Letters*, **2012**, 7, 563	5	8
95	Properties of thermally oxidized and nitrided Zr-oxynitride thin film on 4H-SiC in diluted N2O ambient. *Materials Chemistry and Physics*, **2012**, 136, 624-637	4.4	8
94	Effects of temperature and crucible height on the synthesis of 6H-SiC nanowires and nanoneedles. *Journal of Alloys and Compounds*, **2009**, 481, 345-348	5.7	8
93	Electrical Properties of Atomic-Layer-Deposited La2O3/Thermal-Nitrided SiO2 Stacking Dielectric on 4H-SiC(0001). *Materials Science Forum*, **2007**, 556-557, 643-646	0.4	8
92	Properties of Nitrided Oxides on SiC. *Advanced Texts in Physics*, **2004**, 373-386		8
91	Investigation of honey thin film as a resistive switching material for nonvolatile memories. *Materials Letters*, **2020**, 271, 127796	3.3	7
90	Effects of drying temperature on tomato-based thin film as self-powered UV photodetector. *Applied Surface Science*, **2018**, 445, 186-196	6.7	7
89	Effects of oxidation and nitridation temperatures on electrical properties of sputtered Zr thin film based on Si in N2O ambient. *Electronic Materials Letters*, **2012**, 8, 47-51	2.9	7
88	A novel silver–aluminium high-temperature die attach nanopaste system: the effects of organic additives content on post-sintered attributes. *Journal of Materials Science: Materials in Electronics*, **2013**, 24, 2678-2688	2.1	7
87	Effect of Oxidation Time on Thermally Grown Oxide on GaN. *Journal of Materials Engineering and Performance*, **2013**, 22, 1341-1347	1.6	7
86	Comparison of oxidized/nitrided Zr thin films on Si and SiC substrates. *Ceramics International*, **2013**, 39, S475-S479	5.1	7
85	Synthesis and characterization of silica–titania nanocomposite via a combination of sol–gel and mechanochemical process. *Journal of Alloys and Compounds*, **2008**, 466, 304-307	5.7	7
84	Effects of precursor aging and post-deposition treatment time on photo-assisted sol–gel derived low-dielectric constant SiO2 thin film on Si. *Microelectronics Journal*, **2007**, 38, 227-230	1.8	7
83	Titanium Dioxide/Polyvinyl Alcohol/Cork Nanocomposite: A Floating Photocatalyst for the Degradation of Methylene Blue under Irradiation of a Visible Light Source. *ACS Omega*, **2021**, 6, 14493-14503	3.9	7

82	Green synthesis of iron oxide thin-films grown from recycled iron foils. *Materials Science in Semiconductor Processing*, **2015**, 29, 294-299	4.3	6
81	An improved three-point bending test method for the investigation of nanosecond laser dicing of ultrathin Si dies with Cu stabilization layer. *Materials Characterization*, **2018**, 136, 29-40	3.9	6
80	Design and synthesis of mesoporous ZrO2 thin films using surfactant Pluronic P123 via sol-gel technique. *Journal of the Ceramic Society of Japan*, **2011**, 119, 517-521	1	6
79	Effect of process parameters on size, shape, and distribution of Sb2O3 nanoparticles. *Journal of Materials Science*, **2011**, 46, 5129-5139	4.3	6
78	Effects of rapid thermal annealing on Al2O3/SiN reaction barrier layer/thermal-nitrided SiO2 stacking gate dielectrics on n-type 4H-SiC. *Applied Physics Letters*, **2010**, 96, 122108	3.4	6
77	FORTHCOMING GALLIUM NITRIDE BASED POWER DEVICES IN PROMPTING THE DEVELOPMENT OF HIGH POWER APPLICATIONS. *Modern Physics Letters B*, **2011**, 25, 77-88	1.6	6
76	Current Conduction Mechanisms in RF-Magnetron Sputtered Y2O3 Gate on GaN Under Different Post-Deposition Annealing Ambient. *Science of Advanced Materials*, **2013**, 5, 1816-1827	2.3	6
75	Annealing temperature-dependent crystallinity and photocurrent response of anodic nanoporous iron oxide film. *Journal of Materials Research*, **2016**, 31, 1681-1690	2.5	5
74	Investigation of thermally grown oxide on 4H-SiC by a combination of H2O and HNO3 vapor with varied HNO3 solution heating temperature. *Applied Surface Science*, **2013**, 285, 795-804	6.7	5
73	Effect of Nanosecond Laser Dicing on the Mechanical Strength and Fracture Mechanism of Ultrathin Si Dies With Cu Stabilization Layer. *IEEE Transactions on Components, Packaging and Manufacturing Technology*, **2015**, 5, 1885-1897	1.7	5
72	Schottky barrier height engineering of Al contacts on Si by embedded Au nanoparticles. *Microelectronic Engineering*, **2015**, 133, 110-119	2.5	5
71	Effect of oxidation temperature on physical properties of thermally grown oxide on GaN in N2O ambient. *Materials Chemistry and Physics*, **2012**, 137, 381-388	4.4	5
70	Influence of post-deposition annealing on metal-organic decomposed lanthanum cerium oxide film **2011**,		5
69	Effects of Post-Deposition Annealing Temperature on Band Alignment and Electrical Characteristics of Lanthanum Cerium Oxide on 4H-SiC. *Materials Research Society Symposia Proceedings*, **2012**, 1433, 7		5
68	Resistive switching behaviour in a polymannose film for multistate non-volatile memory application. *Journal of Materials Chemistry C*, **2021**, 9, 1437-1450	7.1	5
67	Growth of gold nanoparticles using aluminum template via low-temperature hydrothermal method for memory applications. *Journal of Materials Science: Materials in Electronics*, **2015**, 26, 6484-6494	2.1	4
66	Direct formation of AuNPs thin film using thermal evaporated zinc as sacrificial template in hydrothermal method. *Journal of Materials Science: Materials in Electronics*, **2014**, 25, 2227-2236	2.1	4
65	Effects of applied voltage on the properties of anodic zirconia thin film on (100) silicon. *Thin Solid Films*, **2012**, 522, 117-124	2.2	4

64	Effects of Thermally Oxidized-SiN Gate Oxide on 4H-SiC Substrate. *Electrochemical and Solid-State Letters*, **2007**, 10, H327		4
63	Memory properties of Au nanoparticles prepared by tuning HAuCl4 concentration using low-temperature hydrothermal reaction. *Thin Solid Films*, **2016**, 615, 84-90	2.2	3
62	Investigation of SiO2 film growth on 4H-SiC by direct thermal oxidation and postoxidation annealing techniques in HNO3 & H2O vapor at varied process durations. *Thin Solid Films*, **2014**, 570, 138-149	2.2	3
61	Aloe vera in active and passive regions of electronic devices towards a sustainable development **2017**,		3
60	A diplotype in the lymphotoxin alpha gene is associated with differential expression of LTA mRNA induced by Gram-positive and Gram-negative bacteria. *International Journal of Immunogenetics*, **2007**, 34, 157-60	2.3	3
59	Stress and thermal characterization of 4H-SiC microelectromechanical structures. *Materials Letters*, **2017**, 191, 196-199	3.3	2
58	Fracture strength and microstructural study of ultrathin Si die with Cu backside layer diced with picosecond laser. *Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing*, **2019**, 759, 785-796	5.3	2
57	Mechanism study of SiO2 layer formation and separation at the Si die sidewall during nanosecond laser dicing of ultrathin Si wafers with Cu backside layer. *Applied Physics A: Materials Science and Processing*, **2020**, 126, 1	2.6	2
56	Ultralow Voltage Operation of ${rm Al}/{rm La}_{x}{rm Ce}_{1-x}{rm O}_{z}/{rm 4Hhbox{-}SiC}$ for Oxygen Sensing. *IEEE Electron Device Letters*, **2013**, 34, 1430-1432	4.4	2
55	Post-Deposition Annealing in Nitrous Oxide Ambient of RF-Magnetron Sputtered Y2O3 Film on Silicon Substrate. *Advanced Materials Research*, **2014**, 1024, 360-363	0.5	2
54	Influence of post-deposition annealing time on oxygen gas sensing behaviour of Al/La0□50Ce0□50O1□75/Si metal-oxide-semiconductor capacitor. *Materials Research Innovations*, **2014**, 18, S6-490-S6-494	1.9	2
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52	Effect of spent bleaching earth based bio organic fertilizer on growth, yield and quality of eggplants under field condition **2013**,		2
51	Effects of SiO2 Nanoparticles on Dielectric Characteristic of Aloe Vera Paste. *Advanced Materials Research*, **2013**, 858, 74-79	0.5	2
50	Effects of wet-oxidized 4H-SiC annealed in HNO3/H2O vapour. *Microelectronics International*, **2013**, 31, 42-53	0.8	2
49	Formation of Anodic Oxide Nanotubes in H2O2 - Fluoride Ethylene Glycol Electrolyte as Template for Electrodeposition of □Fe2O3. *Advanced Materials Research*, **2013**, 832, 333-337	0.5	2
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